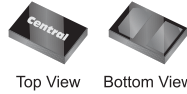


**CFSH-4**  
**SURFACE MOUNT**  
**SILICON SCHOTTKY DIODE**



[www.centrasemi.com](http://www.centrasemi.com)

**TLP**™  
Tiny  
Leadless  
Package



Top View    Bottom View  
**SOD-882L CASE**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CFSH-4 is a high quality Schottky Diode designed for applications where ultra small size and power dissipation are prime requirements. Packaged in a Tiny Leadless Package™, TLP™, this component provides performance characteristics suitable for the most demanding size constrained applications.

**MARKING CODE: L**

**FEATURES:**

- Device is **Halogen Free** by design
- Current ( $I_O=200\text{mA}$ )
- Low Forward Voltage Drop ( $V_F=0.35\text{V TYP @ }1.0\text{mA}$ )
- Low Reverse Current ( $25\text{nA TYP @ }30\text{V}$ )
- Extremely Fast Switching (5ns Max)
- Small TLP™, 1mm x 0.6mm x 0.4mm, SOD-882L, ultra low profile, Leadless Surface Mount package.

**APPLICATIONS:**

- DC / DC Converters
- Voltage Clamping
- Protection Circuits
- Battery powered applications including Cell Phones, Digital Cameras, Pagers, PDAs, Laptop Computers, etc.

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Peak Repetitive Reverse Voltage  
Average Forward Current  
Peak Forward Surge Current,  $t_p=8.3\text{ms}$   
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

**SYMBOL**

$V_{RRM}$                     40  
 $I_O$                          200  
 $I_{FSM}$                     600  
 $P_D$                         100  
 $T_J, T_{stg}$                 -65 to +125  
 $\theta_{JA}$                       1000

**UNITS**

V  
mA  
mA  
mW  
°C  
°C/W

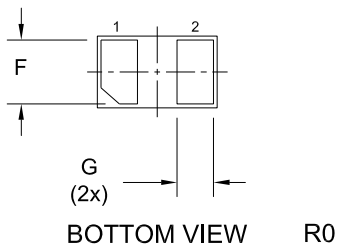
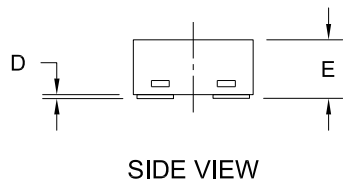
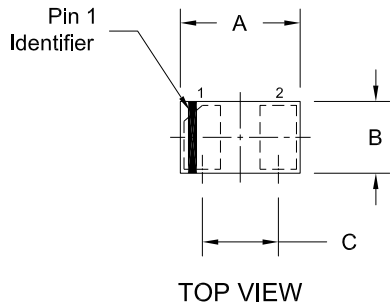
**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=30\text{V}$		25	200	nA
$BV_R$	$I_R=10\mu\text{A}$	40			V
$V_F$	$I_F=1.0\text{mA}$		0.35	0.38	V
$V_F$	$I_F=15\text{mA}$		0.55	0.65	V
$V_F$	$I_F=40\text{mA}$		0.77	1.00	V
$C_T$	$V_R=0\text{V}, f=1.0\text{MHz}$			5.0	pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

**CFSH-4**  
**SURFACE MOUNT**  
**SILICON SCHOTTKY DIODE**



**SOD-882L CASE - MECHANICAL OUTLINE**



<b>DIMENSIONS</b>				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.041	0.95	1.05
B	0.022	0.026	0.55	0.65
C	0.026		0.65	
D	0.000	0.002	0.00	0.05
E	0.012	0.016	0.30	0.40
F	0.018	0.022	0.45	0.55
G	0.008	0.012	0.20	0.30

SOD-882L (REV:R0)

**LEAD CODE:**

- 1) CATHODE
- 2) ANODE

**MARKING CODE: L**

R2 (4-January 2010)